

**DECLARATION OF SOLE INVENTOR FOR PATENT APPLICATION**

As the below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and sole inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled: "Methods of Forming Material on a Substrate, and a Method of Forming a Field Effect Transistor Gate Oxide on a Substrate", the specification of which is attached hereto.

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims.

I acknowledge the duty to disclose information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations § 1.56.

**PRIOR FOREIGN APPLICATIONS:**

I hereby state that no applications for foreign patents or inventor's certificates have been filed prior to the date of execution of this declaration.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such


willful false statement may jeopardize the validity of the application or any patent issued therefrom.

\* \* \* \* \*

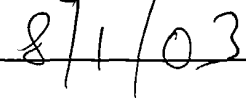
Full name of sole inventor:

**Gurtej S. Sandhu**

Inventor's Signature:



Date:



Residence:

**Boise, Idaho**

Citizenship:

**United Kingdom**

Post Office Address:

**2964 East Parkriver Drive, Boise, ID 83706**

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. .... Unknown  
 Filing Date .... Filed Herewith  
 Inventor .... Gurtej S. Sandhu  
 Assignee .... Micron Technology, Inc.  
 Group Art Unit .... Unknown  
 Examiner .... Unknown  
 Attorney's Docket No. .... MI22-2194  
 Title: Methods of Forming Material on a Substrate, and a Method of Forming a  
 Field Effect Transistor Gate Oxide on a Substrate

**POWER OF ATTORNEY BY ASSIGNEE AND CERTIFICATE BY ASSIGNEE**  
**UNDER 37 CFR § 3.73(b)**

To: Assistant Commissioner for Patents  
 Washington, D.C. 20231

Sir:

**MICRON TECHNOLOGY, INC.,** the Assignee of the entire right, title and  
 interest in the above-identified patent application by assignment attached hereto,  
 hereby appoints the attorneys and agents of the firm of WELLS ST. JOHN P.S.,  
 listed as follows:

David P. Roberts	Reg. No. 23,032
Randy A. Gregory	Reg. No. 30,386
Mark S. Matkin	Reg. No. 32,268
Deepak Malhotra	Reg. No. 33,560
Mark W. Hendricksen	Reg. No. 32,356
David G. Latwesen	Reg. No. 38,533
George G. Grigel	Reg. No. 31,166
Keith D. Grzelak	Reg. No. 37,144
James D. Shaurette	Reg. No. 39,833
James E. Lake	Reg. No. 44,854
D. Brent Kenady	Reg. No. 40,045
Jennifer J. Taylor	Reg. No. 48,711
Robert C. Hyta	Reg. No. 46,791
Satheesh K. Karra	Reg. No. 40,246

and also attorneys Michael L. Lynch (Reg. No. 30,871), Charles B. Brantley II  
 (Reg. No. 38,086) and Russel D. Slifer (Reg. No. 39,838) of Micron

Technology, Inc., as its attorneys with full power of substitution to prosecute this application and transact all business in the Patent and Trademark Office connected therewith.

The Assignee certifies that the above-identified Assignment has been reviewed and to the best of Assignee's knowledge and belief, title is in the Assignee, and a copy of the Assignment is submitted herewith.

Please direct all correspondence regarding this application to:

Customer No. 021567  
Wells St. John P.S.  
Attn: Mark S. Matkin  
601 West First Avenue, Suite 1300  
Spokane, WA 99201-3828  
Telephone: (509) 624-4276  
Facsimile: (509) 838-3424

MICRON TECHNOLOGY, INC.

Dated: Aug 4, 2003

By: [Signature]

Name: Michael L. Lynch, Esq.

Title: Chief Patent Counsel

*Attachments: Copy of Assignment; Copy of Board of Directors' Resolution*